

Transistor

4V Drive Nch MOS FET

RSS085N05

●Structure

Silicon N-channel
MOS FET

●Features

- 1) Built-in G-S Protection Diode.
- 2) Small and Surface Mount Package (SOP8).

●Applications

Power switching , DC / DC converter, Inverter

●Packaging dimensions

Type	Package	Taping
	Code	TB
	Basic ordering unit (pieces)	2500
RSS085N05		○

●Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		V_{DS}	45	V
Gate-source voltage		V_{GS}	20	V
Drain current	Continuous	I_D	±8.5	A
	Pulsed	I_{DP} *1	±34	A
Source current (Body diode)	Continuous	I_S	1.6	A
	Pulsed	I_{SP} *1	34	A
Total power dissipation		P_D *2	2	W
Chanel temperature		T_{ch}	150	°C
Range of Storage temperature		T_{stg}	-55 to +150	°C

*1 $PW \leq 10\mu s$, Duty cycle $\leq 1\%$

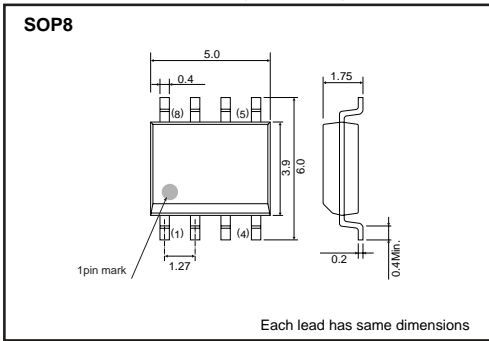
*2 Mounted on a ceramic board

●Thermal resistance

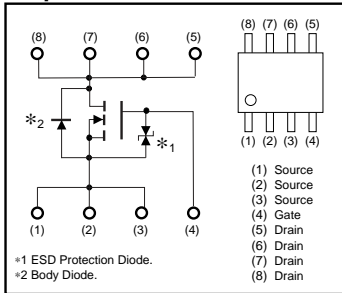
Parameter	Symbol	Limits	Unit
Chanel to ambient	$R_{th(ch-a)}$ *	62.5	°C/W

* Mounted on a ceramic board

●External dimensions (Unit : mm)



●Equivalent circuit



* A protection diode is included between the gate and the source terminals to protect the diode against static electricity when the product is in use. Use a protection circuit when the fixed voltage are exceeded.

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●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	—	—	10	μA	$V_{GS}=20V, V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR) DSS}$	45	—	—	V	$I_D=1mA, V_{GS}=0V$
Zero gate voltage drain current	I_{DSS}	—	—	1	μA	$V_{DS}=45V, V_{GS}=0V$
Gate threshold voltage	$V_{GS(th)}$	1.0	—	2.5	V	$V_{DS}=10V, I_D=1mA$
Static drain-source on-state resistance	$R_{DS(on)}^*$	—	13	18	m Ω	$I_D=8.5A, V_{GS}=10V$
		—	16	23	m Ω	$I_D=8.5A, V_{GS}=4.5V$
		—	18	25	m Ω	$I_D=8.5A, V_{GS}=4V$
Forward transfer admittance	$ Y_{fs} ^*$	7.0	—	—	S	$V_{DS}=10V, I_D=8.5A$
Input capacitance	C_{iss}	—	1500	—	pF	$V_{DS}=10V$
Output capacitance	C_{oss}	—	350	—	pF	$V_{GS}=0V$
Reverse transfer capacitance	C_{rss}	—	170	—	pF	$f=1MHz$
Turn-on delay time	$t_{d(on)}^*$	—	19	—	ns	$V_{DD} \doteq 25V$ $I_D=4.0A$ $V_{GS}=10V$ $R_L=6.3\Omega$ $R_G=10\Omega$
Rise time	t_r^*	—	25	—	ns	
Turn-off delay time	$t_{d(off)}^*$	—	71	—	ns	
Fall time	t_f^*	—	24	—	ns	
Total gate charge	Q_g^*	—	15.3	21.4	nC	$V_{DD} \doteq 25V \quad V_{GS}=5V$
Gate-source charge	Q_{gs}^*	—	4.4	—	nC	$I_D=8.5A$
Gate-drain charge	Q_{gd}^*	—	6.0	—	nC	$R_L=2.9\Omega \quad R_G=10\Omega$

*Pulsed

Body diode characteristics (Source-Drain) (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_{SD}^*	—	—	1.2	V	$I_S=8.5A, V_{GS}=0V$

*Pulsed

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●Electrical characteristic curves

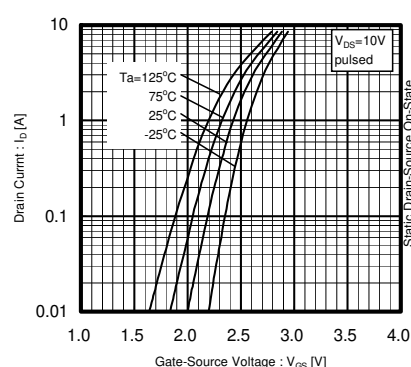


Fig.1 Typical Transfer Characteristics

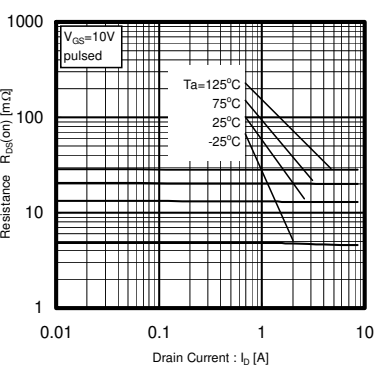


Fig.2 Static Drain-Source On-State Resistance vs. Drain Current (1)

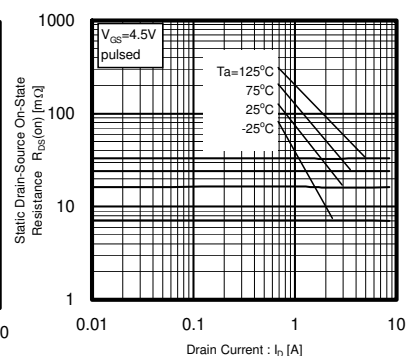


Fig.3 Static Drain-Source On-State Resistance vs. Drain Current (2)

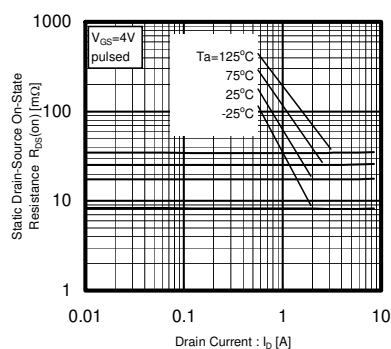


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current (3)

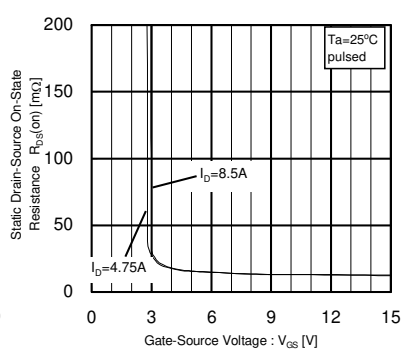


Fig.5 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

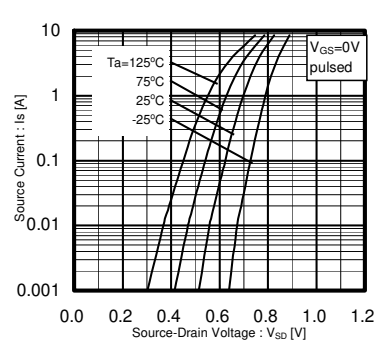


Fig.6 Source-Current vs. Source-Drain Voltage

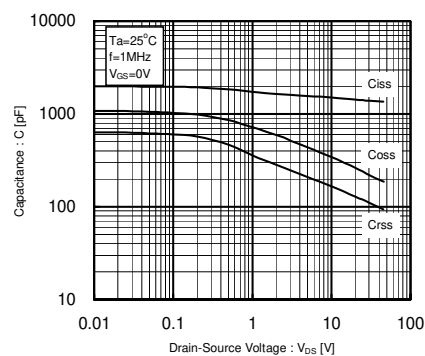


Fig.7 Typical capacitance vs. Source-Drain Voltage

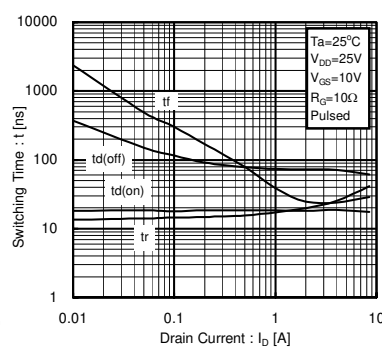


Fig.8 Switching Characteristics

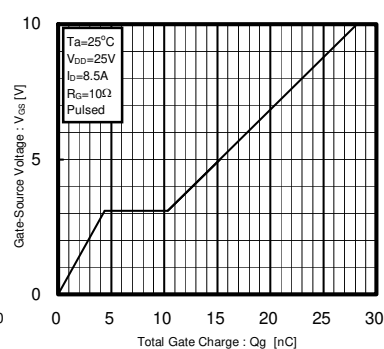


Fig.9 Dynamic Input Characteristics

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●Measurement circuits

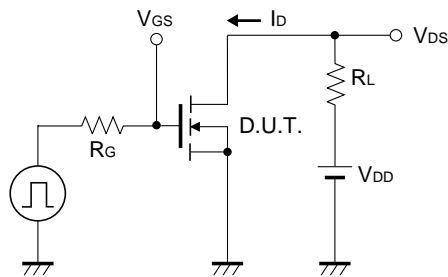


Fig.10 Switching Time Test Circuit

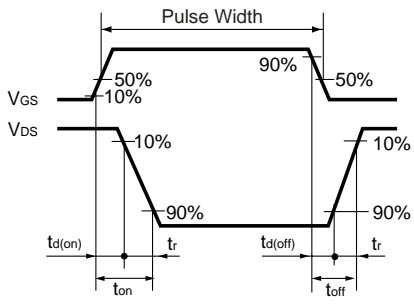


Fig.11 Switching Time Waveforms

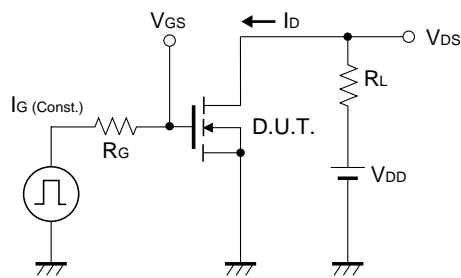


Fig.12 Gate Charge Test Circuit

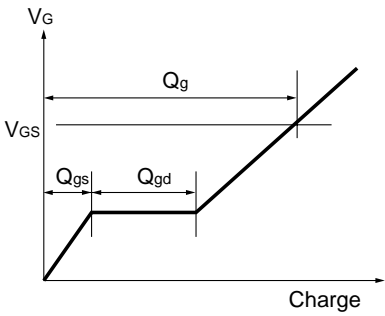


Fig.13 Gate Charge Waveform

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